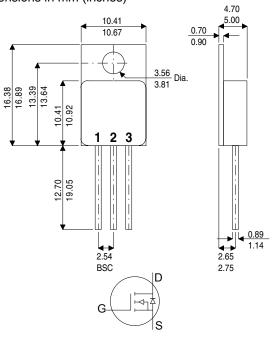


IRFY340

MECHANICAL DATA

Dimensions in mm (inches)



TO-220M (TO-257AB)

Pin 1 - Gate Pin 2 - Drain Pin 3 - Source

N-CHANNEL POWER MOSFET FOR HI-REL APPLICATIONS

 $\begin{array}{ll} \text{BV}_{\text{DSS}} & 400\text{V} \\ \text{I}_{\text{D}} & 8.7\text{A} \\ \text{R}_{\text{ns(on)}} & 0.55\Omega \end{array}$

FEATURES

- HERMETICALLY SEALED TO-220 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- ALL LEADS ISOLATED FROM CASE
- LIGHTWEIGHT
- SCREENING OPTIONS AVAILABLE

ABSOLUTE MAXIMUM RATINGS T_{CASE} = 25°C unless otherwise stated

V _{DS}	Drain - Source Voltage	400V
V_{gs}	Gate - Source Voltage	±20V
I _D	Drain Current - Continuous ($T_c = 25^{\circ}C$)	8.7A
I _D	Drain Current - Continuous (T _c = 100°C)	5.5A
I _{DM}	Drain Current - Pulsed ¹	35A
$P_{_{D}}$	Total Power Dissipation at T _{case} ≤ 25°C	100W
	De-rate Linearly above 25°C	0.8W/°C
T_{j}, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150°C
T	Lead Temperature (for 5 sec)	300°C
$R_{thj\text{-case}}$	Thermal Resistance Junction - Case	1.25°C/W

NOTES:

- 1) Pulse Width limited by maximum junction temperature.
- 2) Pulse Test: Pulse Width ≤ 380μS, Duty Cycle, δ 2%

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IRFY340

STATIC ELECTRICAL RATINGS (T_{case}=25°C unless otherwise stated)

	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V$ $I_{D} = 1.0mA$	400	-	1	V
$\Delta BV_{\mathtt{DSS}}$	Temperature Coefficient of	Reference to 25°C		0.46	_	V/°C
ΔT_{J}	Breakdown Voltage	$I_D = 1.0 \text{mA}$	-	0.40	-	V/ C
I _{DSS}	Zero Gate Voltage Drain Current	V_{DS} =320V V_{GS} = 0V	-	-	25	
		T _J = 125°C	-	-	250	μA
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V$ $V_{DS} = 0V$	-	-	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_{D} = 250 \mu A$	2.0	-	4.0	٧
R _{DS(ON)}	Drain – Source On State Resistance	$V_{GS} = 10V$ $I_{D} = 5.5A$	-	-	0.55	Ω
		$V_{GS} = 10V$ $I_D = 8.7A$	-	-	0.63	Ω
g _{FS}	Forward Transconductance ²	$V_{DS} \ge 15V$ $I_{D} = 5.5A$	4.9	-	-	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 25V f = 1.0MHz	$V_{GS} = 0V$	-	1400	-	pF
C _{oss}	Output Capacitance			-	350	-	
C _{rss}	Reverse Transfer Capacitance			-	230	-	
Q_{g}	Total Gate Charge ²	V _{DS} = 200V V _{GS} = 10V	I _D = 8.7A	ī	-	65	nC
Q_{gs}	Gate – Source Charge ²			Ü	•	10	
Q_{gd}	Gate – Drain Charge ²			Ü	•	40.5	
$T_{d(on)}$	Turn-On Delay	$V_{DD} = 200V$ $R_{G} = 9.1\Omega$	$I_{D} = 8.7A$ $V_{GS} = 10V$	Ü	•	25	ns
t,	Rise Time			Ü	•	92	
$T_{d(off)}$	Turn-Off Delay Time				-	79	
t _f	Fall Time				-	58	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

Is	Continuous Source Current (MAX)			-	-	8.7	Α
I _{SM}	Pulsed Source Current (MAX)			-	-	35	^
V _{SD}	Diode Forward Voltage ²	$V_{GS} = 0V$	$I_{s} = 8.7A$	-	-	1.5	V
t _{rr}	Reverse Recovery Time ²	$V_{GS} = 0V$	I _s = 8.7A	-	-	600	ns
Q _{rr}	Reverse Recovery Charge ²	di/dt=100A/µs	$V_{\text{DD}} \leq 50V$	-	-	5.6	μC
T _{on}	Forward Turn-On Time			Negligible			

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